

DOCUMENT CHANGE REQUEST

514 DCR number Changes required for: General Originator: S Jeffery - ESCC Date: 2009/05/06 Organisation: ESA/ESTEC Date sent: 2009/05/06 Status: IMPLEMENTED Title: Transistors High Power NPN, based on types 2N5664 through 2N5667 2 Number: 5203/038 Issue: Other documents affected: Page: See attachment Paragraph: See attachment Original wording: Proposed wording: Update the Maximum Ratings table (see the attachment for details) so that this detail spec is clear, complete and the content and format is in-line with other detail specifications for similar Part Types. Justification: Improve the content and clarity of the spec. Attachments: 5203038_Issue_3_-_Draft_A.pdf, null Modifications: Page 6: Original Note 2 to Maximum Ratings – add ", and any handling," between "testing" and "performed". Approval signature: 12. (c f(an-9 Date signed: 2009-05-06

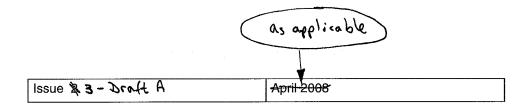


Pages 1 to 20

TRANSISTORS, HIGH POWER, NPN

BASED ON TYPE 2N5664, 2N5665, 2N5666 AND 2N5667

ESCC Detail Specification No. 5203/038







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as applicable

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DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

| Specification up issued to incorporate editorial and technical changes per DCR. | To State of Section |
|---|---------------------|

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1.5 **MAXIMUM RATINGS**

The maximum ratings shall not be exceeded at any time during use or storage. Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

| Characteristics | Symbols | Maximum Ratings | Unit | Remarks |
|--|------------------|-----------------|------------|--------------------------------------|
| Collector-Base Voltage Variants 01, 02, 05, 06, 09, 10 Variants 03, 04, 11 | V _{CBO} | 250 400 | V | Over T _{op} |
| Collector-Emitter Voltage Variants 01, 02, 05, 06, 09, 10 Variants 03, 04, 11 | V _{CEO} | 200 300 | V | Over T _{op} Note ৠ 2 |
| Emitter-Base Voltage | V _{EBO} | 6 | ٧ | Over T _{op} |
| Collector Current | I _C | 5 | Α | Continuous Note 3, 2 |
| Base Current | Ι _Β | 1 | Α | Continuous |
| Rower Dissipation For TO-66 For TQ-5 and TO-392 | \$ 50 | 30 15 | 8 | At T _{case} ± +106°C Note 1 |
| Operating Temperature Range | T _{op} | -65 to +200 | °C | Note à ₫ |
| Storage Temperature Range | T _{stg} | -65 to +200 | °C | Note & 1 |
| Soldering Temperature | T _{sol} | +260 | °C | Note ¾ 3 |
| Thermal Resistance Junction to Case For TO-66 For TO-5 and TQ-39 | | 3,3 6.7 | ★ / | |

See attached

For T_{case} > +100°C, derate linearly to 0W at +200°C.

For Variants with tin-lead plating or hot solder dip lead finish all testing performed at T_{amb} > +125°C

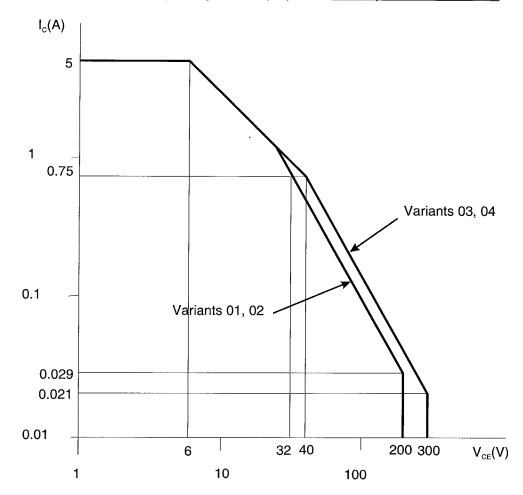
| Power Dissipation | P _{tot1} | | W | At T _{amb} ≤ +25°C |
|---------------------|-------------------|-------|------|-------------------------------|
| For TO-66 | | 2.5 | | 22 |
| For TO-5 and TO-39 | | 1.2 | | |
| | P _{tot2} | | W | At T _{case} ≤ +100°C |
| For TO-66 | | 30 | | |
| For TO-5 and TO-39 | | 15 | | |
| Thermal Resistance, | | | | |
| Junction-to-Ambient | $R_{th(j-a)}$ | | °c/w | |
| For TO-66 | | 70 | | |
| For TO-5 and TO-39 | | 145.8 | | |
| Thermal Resistance, | | | | |
| Junction-to-Case | $R_{th(j-c)}$ | | °c/W | |
| For TO-66 | | 3.3 | | |
| For TO-5 and TO-39 | | 6.7 | | |



shall be carried out in a 100% inert atmosphere.

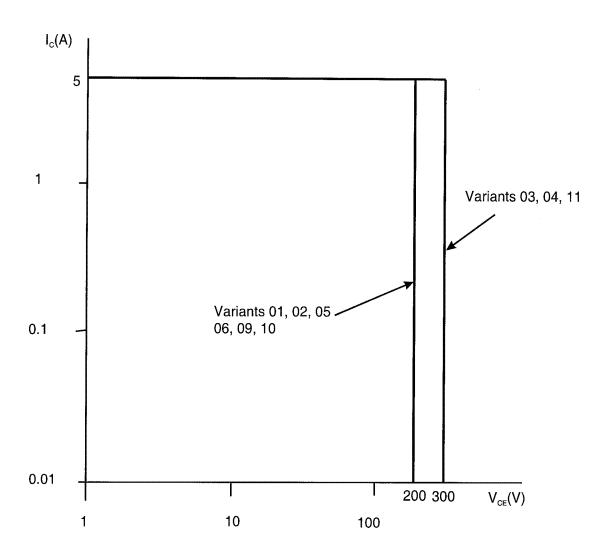
2 · 🦠 Safe Operating Area applies as follows:

Maximum Safe Operating Area Graph (Continuous DC) for Variants 01 to 04



Maximum Safe Operating Area Graph (Continuous DC) for Variants 05, 06, 09, 10 and 11





3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

Consolidated notes are given following the case drawings and dimensions.